

1N4454



DO-35

High Conductance Ultra Fast Diode

Sourced from Process 1R. See MMBD1201-1205 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
W_{IV}	Working Inverse Voltage	50	V
I_O	Average Rectified Current	200	mA
I_F	DC Forward Current	400	mA
i_F	Recurrent Peak Forward Current	600	mA
$i_{(surge)}$	Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond	1.0 4.0	A A
T_{stg}	Storage Temperature Range	-65 to +200	°C
T_J	Operating Junction Temperature	175	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 200 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		1N4454	
P_D	Total Device Dissipation Derate above 25°C	500 3.33	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	°C/W

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(continued)

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Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
B _V	Breakdown Voltage	I _R = 5.0 μA	75		V
I _R	Reverse Current	V _R = 50 V V _R = 50 V, T _A = 150°C		100 100	nA μA
V _F	Forward Voltage	I _F = 250 μA I _F = 1.0 mA I _F = 2.0 mA I _F = 10 mA	505 550 610	575 650 710 1.0	mV mV mV V
C _O	Diode Capacitance	V _R = 0, f = 1.0 MHz		4.0	pF
T _{RR}	Reverse Recovery Time	I _F = 10 mA, V _R = 1.0 V, I _{rr} = 1.0 mA, R _L = 100 Ω		4.0	nS